

RJK1211DNS

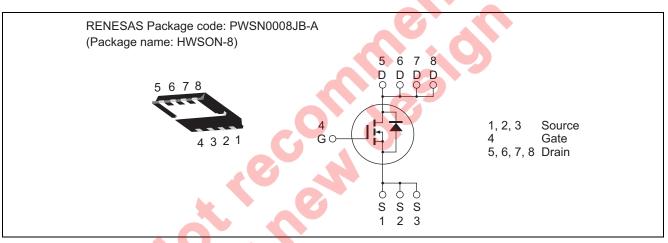
120V, 5A, 130m Ω max. Silicon N Channel Power MOS FET Power Switching

R07DS0090EJ0400 Rev.4.00 Apr 11, 2013

Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance $R_{DS(on)} = 100 \text{ m}\Omega \text{ typ.} (\text{at } V_{GS} = 10 \text{ V})$
- Pb-free
- Halogen-free

Outline



Absolute Maximum Ratings

| | | | $(Ta = 25^{\circ}C)$ | | |
|----------------------------------------|--------------------------------|-------------|----------------------|--|--|
| Item | Symbol | Ratings | Unit | | |
| Drain to source voltage | V _{DSS} | 120 | V | | |
| Gate to source voltage | V _{GSS} | +12, –5 | V | | |
| Drain current | I _D | 5 | А | | |
| Drain peak current | Note1 I _{D(pulse)} | 15 | А | | |
| Body-drain diode reverse drain current | I _{DR} | 5 | А | | |
| Avalanche current | I _{AP} Note 2 | 3 | А | | |
| Avalanche energy | E _{AS} Note 2 | 0.77 | mJ | | |
| Channel dissipation | Pch Note3 | 10 | W | | |
| Channel to case thermal impedance | θch-c ^{Note3} | 12.5 | °C/W | | |
| Channel temperature | Tch | 150 | °C | | |
| Storage temperature | Tstg | -55 to +150 | °C | | |
| Note $A = DW/cAO$ is obtained a cAO/ | | · · | | | |

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tch = 25°C, Rg \geq 50 Ω

3. Tc = 25°C

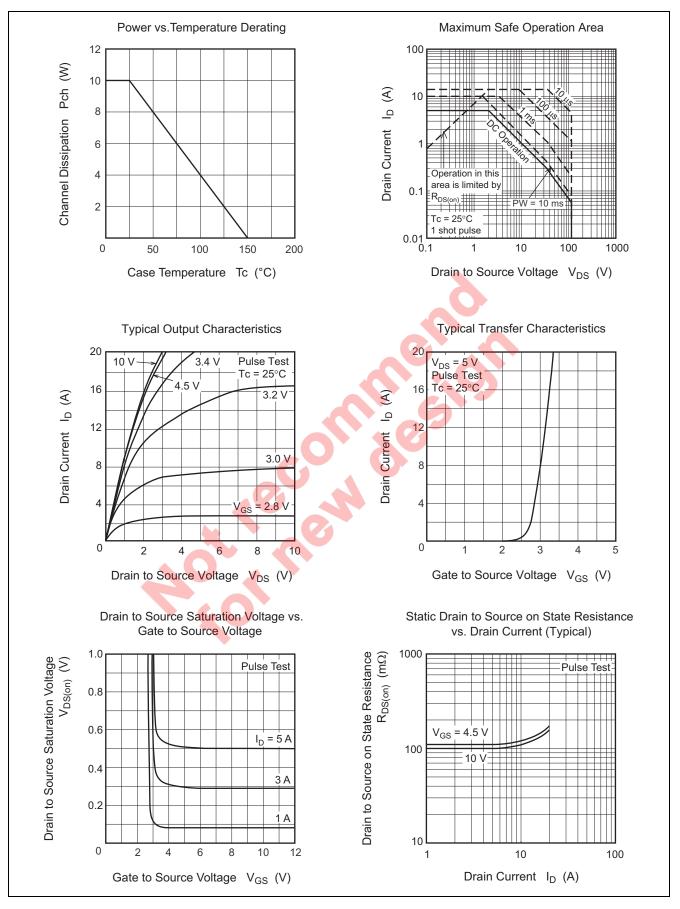


Electrical Characteristics

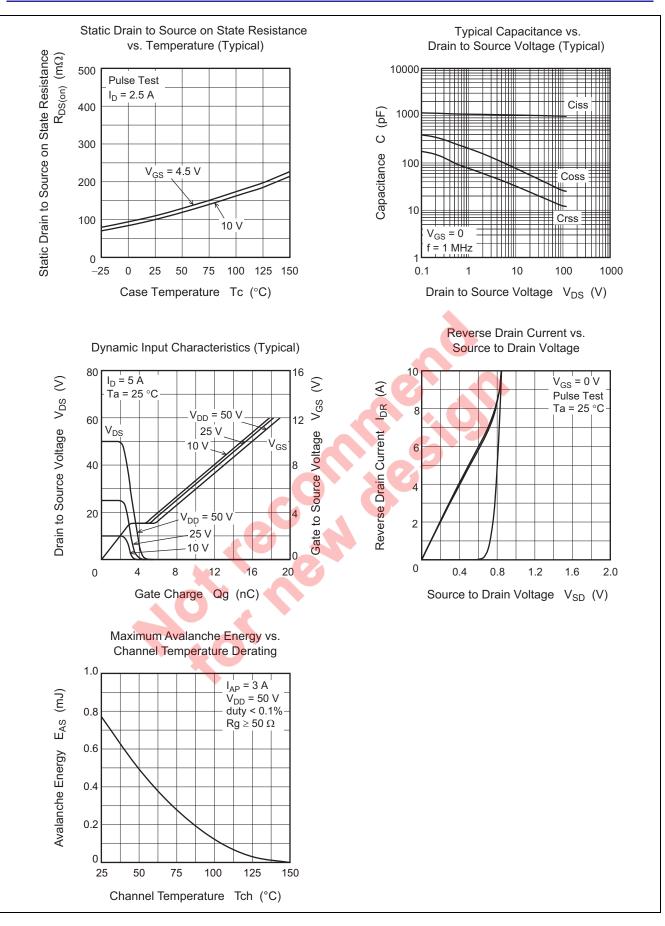
| | 1 | | | | | $(Ta = 25^{\circ}C)$ |
|-----------------------------------|----------------------|-----|------|-------|------|-------------------------------------------------------|
| Item | Symbol | Min | Тур | Max | Unit | Test Conditions |
| Drain to source breakdown voltage | V _{(BR)DSS} | 120 | — | _ | V | $I_{D} = 10 \text{ mA}, V_{GS} = 0$ |
| Gate to source leak current | I _{GSS} | — | — | ± 0.1 | μΑ | V_{GS} = +12, -5 V, V_{DS} = 0 |
| Zero gate voltage drain current | I _{DSS} | _ | — | 10 | μΑ | $V_{DS} = 120 V, V_{GS} = 0$ |
| Gate to source cutoff voltage | V _{GS(off)} | 1.2 | — | 2.5 | V | $V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$ |
| Static drain to source on state | R _{DS(on)} | — | 100 | 130 | mΩ | $I_D = 2.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$ |
| resistance | R _{DS(on)} | — | 110 | 150 | mΩ | $I_D = 2.5 \text{ A}, V_{GS} = 4.5 \text{ V}^{Note4}$ |
| Forward transfer admittance | y _{fs} | _ | 9.0 | _ | S | $I_D = 2.5 \text{ A}, V_{DS} = 5 \text{ V}^{Note4}$ |
| Input capacitance | Ciss | _ | 1070 | _ | pF | V _{DS} = 10 V |
| Output capacitance | Coss | _ | 80 | | pF | $V_{GS} = 0$ |
| Reverse transfer capacitance | Crss | _ | 35 | _ | pF | f = 1 MHz |
| Gate Resistance | Rg | | 1.7 | | Ω | |
| Total gate charge | Qg | | 8.0 | | nC | V _{DD} = 50 V |
| Gate to source charge | Qgs | | 3.0 | | _ nC | V _{GS} = 4.5 V |
| Gate to drain charge | Qgd | _ | 2.0 | | nC | I _D = 5 A |
| Turn-on delay time | t _{d(on)} | _ | 7.8 | - | ns | V _{GS} = 10 V, I _D = 2.5 A |
| Rise time | tr | _ | 2.8 | | ns | V _{DD} ≅ 30 V |
| Turn-off delay time | t _{d(off)} | _ | 38 | | ns | R _L = 12 Ω |
| Fall time | t _f | _ | 2.7 | | ns | Rg = 4.7 Ω |
| Body-drain diode forward voltage | V _{DF} | _ | 0.83 | 1.1 | V | $I_F = 5 \text{ A}, V_{GS} = 0^{\text{Note4}}$ |
| Body-drain diode reverse recovery | t _{rr} | | 40 | — | ns | I _F =5 A, V _{GS} = 0 |
| time | | | | | | di⊧/ dt = 100 A/ µs |
| time Notes: 4. Pulse test | < 05 | | 5 | | | |



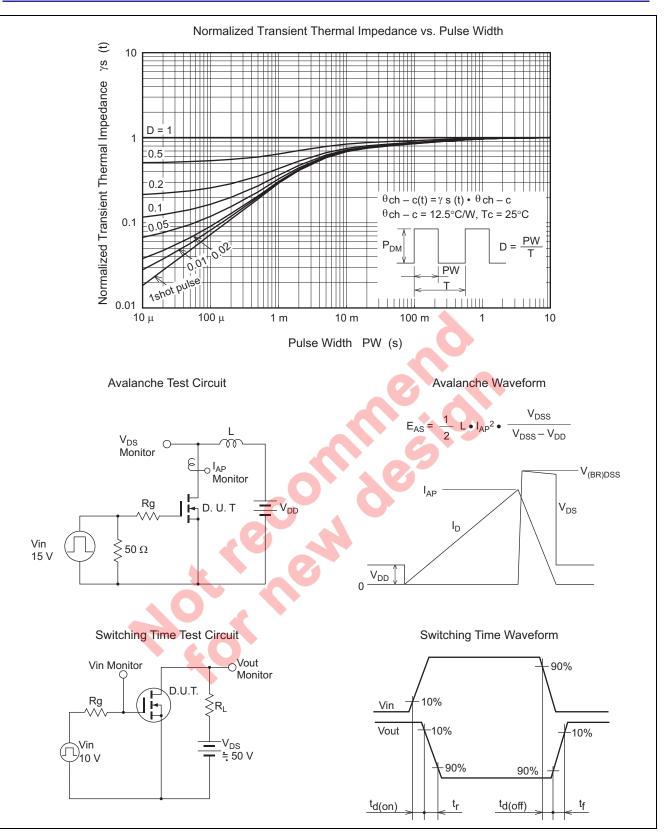
Main Characteristics





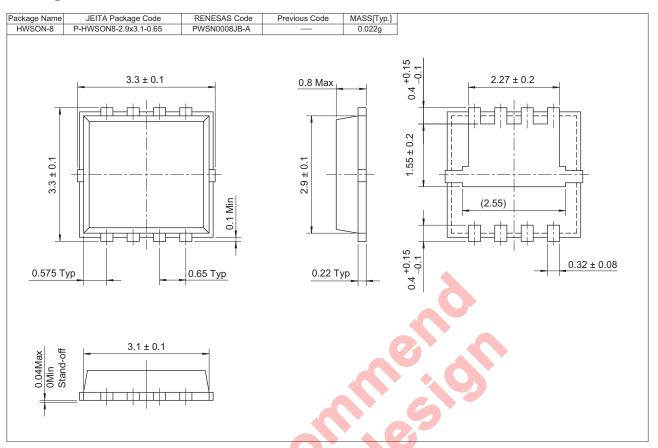








Package Dimensions



Ordering Information

| Orderable Part Number | Quantity | Shipping Container |
|-----------------------|----------|--------------------|
| RJK1211DNS-00-J5 | 5000 pcs | Taping |

Note: The symbol of 2nd "-" is occasionally presented as "#".

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